CMOS Technology

Complementary Metal Oxide Semiconductor (CMOS) is the main technology behind the boom of integrated circuit industry.

The MOS field transistor was proposed by Lilienfield in 1925.

CMOS advantages:
- Low power
- High level of integration

VLSI (very large scale integration) achievable through the use of CMOS technology makes possible to put a lot of functions on a single piece of silicon (possibly an entire system). This increases the reliability of the system on the chip, and lowers the cost.

CMOS technology uses two types of MOS transistors:
- p-type transistor (pMOS) and n-type transistor (nMOS).
The fabrication of a MOS structure requires several chemical processing steps. After those steps a typical MOS structure is composed by the overlapping of the following layers:

diffusion
insulator
poly silicon
metal

[see pictures taken from:
J.P. Uyemura
Physical Design of CMOS Integrated Circuits using L-EDIT
PWS Publishing Company, 1995]
Figure 2.1. The basic lithographic sequence
Figure 2.2. Poly patterning sequence